NSN 5961-01-117-1795

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-117-1795 **Inclosure Material:** Metal or ceramic **Overall Length:** 0.390 inches **Overall Height:** 0.080 inches **Overall Width:** 0.310 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-86 **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 40.0 collector to base voltage, dc all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 1.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Test Data Document:** 17981-012043 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:**

Fiig:

No

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Demilitarization: